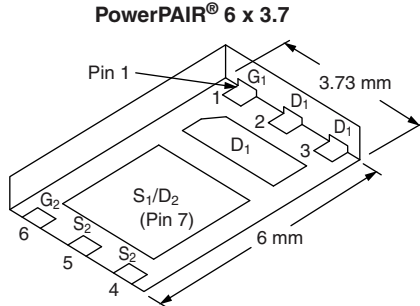




N-Channel 30-V (D-S) MOSFETs

| PRODUCT SUMMARY | | | | |
|-----------------|---------------------|-----------------------------------|--------------------|-----------------------|
| | V _{DS} (V) | R _{DS(on)} (Ω) | I _D (A) | Q _g (Typ.) |
| Channel-1 | 30 | 0.0240 at V _{GS} = 10 V | 12 ^a | 3.8 nC |
| | | 0.0300 at V _{GS} = 4.5 V | 12 ^a | |
| Channel-2 | 30 | 0.0135 at V _{GS} = 10 V | 16 ^a | 7.3 nC |
| | | 0.0170 at V _{GS} = 4.5 V | 16 ^a | |



Ordering Information:
SiZ704DT-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

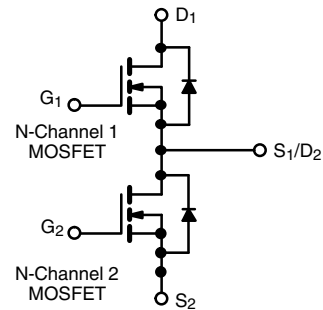
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Notebook System Power
- POL
- Low Current DC/DC



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

| Parameter | Symbol | Channel-1 | Channel-2 | Unit |
|--|-----------------------------------|------------------------|---------------------|----------------------|
| Drain-Source Voltage | V _{DS} | 30 | 30 | V |
| Gate-Source Voltage | V _{GS} | ± 20 | | |
| Continuous Drain Current (T _J = 150 °C) | I _D | T _C = 25 °C | 12 ^a | 16 ^a |
| | | T _C = 70 °C | 12 ^a | 16 ^a |
| | | T _A = 25 °C | 9.4 ^{b, c} | 14 ^{b, c} |
| | | T _A = 70 °C | 7.5 ^{b, c} | 11.2 ^{b, c} |
| Pulsed Drain Current | I _{DM} | 30 | 40 | A |
| Source Drain Current Diode Current | I _S | T _C = 25 °C | 12 ^a | |
| | | T _A = 25 °C | 3.1 ^{b, c} | 3.7 ^{b, c} |
| Single Pulse Avalanche Current | I _{AS} | 10 | 15 | mJ |
| Single Pulse Avalanche Energy | E _{AS} | 5 | 11 | |
| Maximum Power Dissipation | P _D | T _C = 25 °C | 20 | 30 |
| | | T _C = 70 °C | 12.9 | 19 |
| | | T _A = 25 °C | 3.7 ^{b, c} | 4.5 ^{b, c} |
| | | T _A = 70 °C | 2.4 ^{b, c} | 2.9 ^{b, c} |
| Operating Junction and Storage Temperature Range | T _J , T _{stg} | - 55 to 150 | | °C |
| Soldering Recommendations (Peak Temperature) ^{d, e} | | 260 | | |

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Channel-1 | | Channel-2 | | Unit |
|---|-------------------|-----------|------|-----------|------|------|
| | | Typ. | Max. | Typ. | Max. | |
| Maximum Junction-to-Ambient ^{b, f} | R _{thJA} | 26 | 34 | 21 | 28 | °C/W |
| Maximum Junction-to-Case (Drain) | R _{thJC} | 4.7 | 6.2 | 3.2 | 4.2 | |

Notes:

- Package limited.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- See solder profile (www.vishay.com/doc?73257). The PowerPAIR is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 72 °C/W for Channel-1 and 67 °C/W for Channel-2.

| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | | | |
|---|-------------------------|--|--|------|--------|-----------|----------------------|----|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit | | |
| Static | | | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | Ch-1 | 30 | | | V | |
| | | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | Ch-2 | 30 | | | | |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | $I_D = 250\text{ }\mu\text{A}$ | Ch-1 | | 35 | | mV/ $^\circ\text{C}$ | |
| | | $I_D = 250\text{ }\mu\text{A}$ | Ch-2 | | 33 | | | |
| $V_{GS(th)}$ Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | $I_D = 250\text{ }\mu\text{A}$ | Ch-1 | | - 4.5 | | | |
| | | $I_D = 250\text{ }\mu\text{A}$ | Ch-2 | | - 5 | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | Ch-1 | 1 | | 2.5 | V | |
| | | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | Ch-2 | 1.2 | | 2.5 | | |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | Ch-1 | | | ± 100 | nA | |
| | | | Ch-2 | | | ± 100 | | |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$ | Ch-1 | | | 1 | μA | |
| | | $V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$ | Ch-2 | | | 1 | | |
| | | $V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$ | Ch-1 | | | 5 | | |
| | | $V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$ | Ch-2 | | | 5 | | |
| On-State Drain Current ^b | $I_{D(on)}$ | $V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$ | Ch-1 | 20 | | | A | |
| | | $V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$ | Ch-2 | 20 | | | | |
| Drain-Source On-State Resistance ^b | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 7.8\text{ A}$ | Ch-1 | | 0.0200 | 0.0240 | Ω | |
| | | $V_{GS} = 10\text{ V}, I_D = 10\text{ A}$ | Ch-2 | | 0.0105 | 0.0135 | | |
| | | $V_{GS} = 4.5\text{ V}, I_D = 7\text{ A}$ | Ch-1 | | 0.0240 | 0.0300 | | |
| | | $V_{GS} = 4.5\text{ V}, I_D = 7\text{ A}$ | Ch-2 | | 0.0135 | 0.0170 | | |
| Forward Transconductance ^b | g_{fs} | $V_{DS} = 10\text{ V}, I_D = 7.8\text{ A}$ | Ch-1 | | 17 | | S | |
| | | $V_{DS} = 10\text{ V}, I_D = 10\text{ A}$ | Ch-2 | | 24 | | | |
| Dynamic^a | | | | | | | | |
| Input Capacitance | C_{iss} | Channel-1 $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | Ch-1 | | 435 | | pF | |
| | | | Ch-2 | | 846 | | | |
| Output Capacitance | C_{oss} | | Ch-1 | | 95 | | | |
| | | | Ch-2 | | 187 | | | |
| Reverse Transfer Capacitance | C_{rss} | Channel-2 $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | Ch-1 | | 42 | | | |
| | | | Ch-2 | | 72 | | | |
| Total Gate Charge | Q_g | | $V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 7.8\text{ A}$ | Ch-1 | | 8 | 12 | nC |
| | | | $V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 10\text{ A}$ | Ch-2 | | 15.4 | 23 | |
| | | Channel-1 $V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 7.8\text{ A}$ | Ch-1 | | 3.8 | 6 | | |
| | | | Ch-2 | | 7.3 | 11 | | |
| Gate-Source Charge | Q_{gs} | Channel-2 $V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$ | Ch-1 | | 1.4 | | | |
| | | | Ch-2 | | 2.3 | | | |
| Gate-Drain Charge | Q_{gd} | | Ch-1 | | 1.1 | | | |
| | | | Ch-2 | | 2.2 | | | |
| Gate Resistance | R_g | $f = 1\text{ MHz}$ | Ch-1 | 0.6 | 3.2 | 6.4 | Ω | |
| | | | Ch-2 | 0.2 | 0.8 | 1.6 | | |

Notes:

a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.



| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | | | |
|--|--------------|--|--|------|------|------|----|----|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit | | |
| Dynamic^a | | | | | | | | |
| Turn-On Delay Time | $t_{d(on)}$ | Channel-1 $V_{DD} = 15\text{ V}$, $R_L = 2.4\ \Omega$ $I_D \cong 6.3\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 1\ \Omega$ | Ch-1 | | 15 | 30 | ns | |
| | | | Ch-2 | | 15 | 30 | | |
| Rise Time | t_r | $I_D \cong 6.3\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 1\ \Omega$ | Ch-1 | | 12 | 24 | | |
| | | | Ch-2 | | 12 | 24 | | |
| Turn-Off Delay Time | $t_{d(off)}$ | Channel-2 $V_{DD} = 15\text{ V}$, $R_L = 1.5\ \Omega$ $I_D \cong 10\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 1\ \Omega$ | Ch-1 | | 13 | 26 | | |
| | | | Ch-2 | | 13 | 26 | | |
| Fall Time | t_f | $I_D \cong 10\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 1\ \Omega$ | Ch-1 | | 10 | 20 | | |
| | | | Ch-2 | | 10 | 20 | | |
| Turn-On Delay Time | $t_{d(on)}$ | Channel-1 $V_{DD} = 15\text{ V}$, $R_L = 2.4\ \Omega$ $I_D \cong 6.3\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$ | Ch-1 | | 5 | 10 | | |
| | | | Ch-2 | | 9 | 18 | | |
| Rise Time | t_r | $I_D \cong 6.3\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$ | Ch-1 | | 10 | 20 | | |
| | | | Ch-2 | | 9 | 18 | | |
| Turn-Off Delay Time | $t_{d(off)}$ | Channel-2 $V_{DD} = 15\text{ V}$, $R_L = 1.5\ \Omega$ $I_D \cong 10\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$ | Ch-1 | | 15 | 30 | | |
| | | | Ch-2 | | 14 | 28 | | |
| Fall Time | t_f | $I_D \cong 10\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$ | Ch-1 | | 10 | 20 | | |
| | | | Ch-2 | | 8 | 16 | | |
| Drain-Source Body Diode Characteristics | | | | | | | | |
| Continuous Source-Drain Diode Current | I_S | $T_C = 25\text{ }^\circ\text{C}$ | Ch-1 | | | 12 | A | |
| | | | Ch-2 | | | 16 | | |
| Pulse Diode Forward Current ^a | I_{SM} | | Ch-1 | | | 30 | | |
| | | | Ch-2 | | | 40 | | |
| Body Diode Voltage | V_{SD} | $I_S = 6.3\text{ A}$, $V_{GS} = 0\text{ V}$ | Ch-1 | | 0.8 | 1.2 | V | |
| | | $I_S = 3\text{ A}$, $V_{GS} = 0\text{ V}$ | Ch-2 | | 0.78 | 1.2 | | |
| Body Diode Reverse Recovery Time | t_{rr} | Channel-1 $I_F = 6.3\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^\circ\text{C}$ | Ch-1 | | 15 | 30 | ns | |
| | | | Ch-2 | | 17 | 34 | | |
| Body Diode Reverse Recovery Charge | Q_{rr} | | Channel-2 $I_F = 10\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^\circ\text{C}$ | Ch-1 | | 7 | 15 | nC |
| | | | | Ch-2 | | 9.5 | 19 | |
| Reverse Recovery Fall Time | t_a | | Ch-1 | | 9 | | ns | |
| | | | Ch-2 | | 10 | | | |
| Reverse Recovery Rise Time | t_b | | Ch-1 | | 6 | | | |
| | | | Ch-2 | | 7 | | | |

Notes:

- a. Guaranteed by design, not subject to production testing.
 b. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

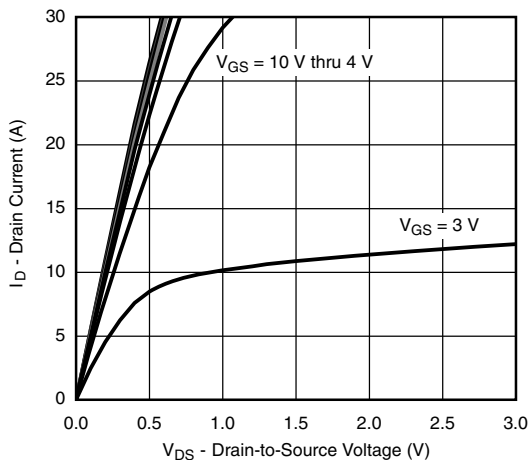
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SiZ704DT

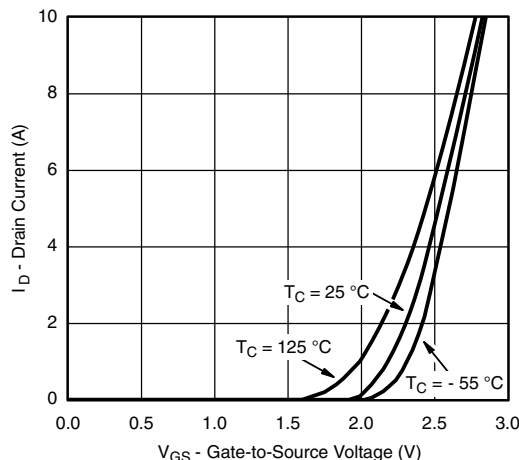
Vishay Siliconix



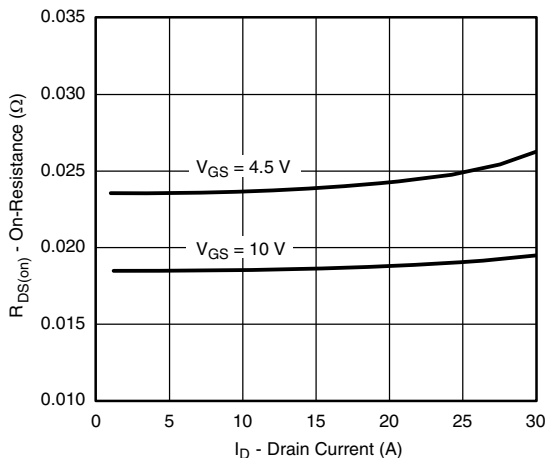
CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



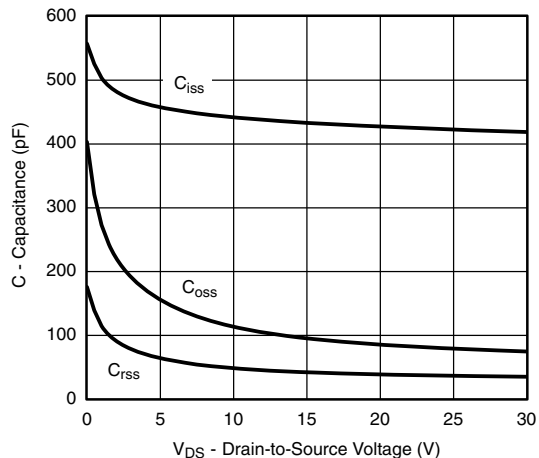
Output Characteristics



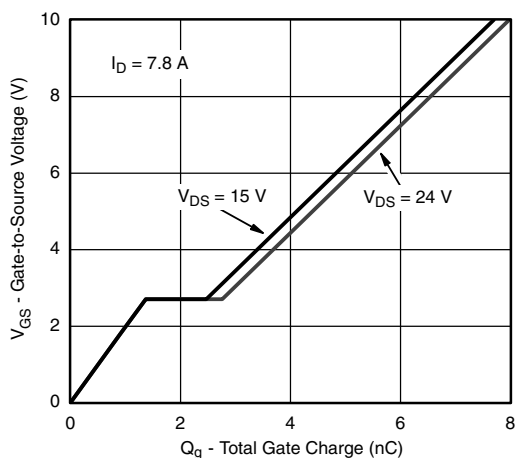
Transfer Characteristics



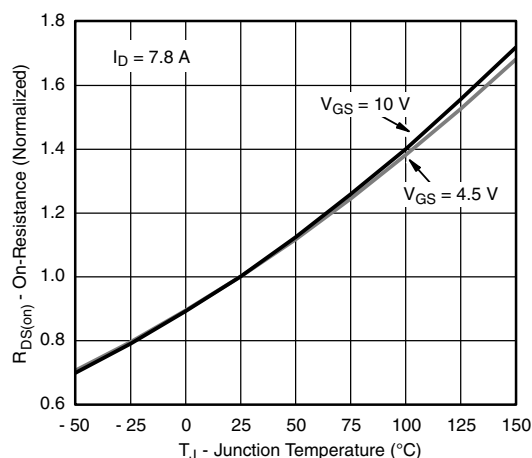
On-Resistance vs. Drain Current



Capacitance



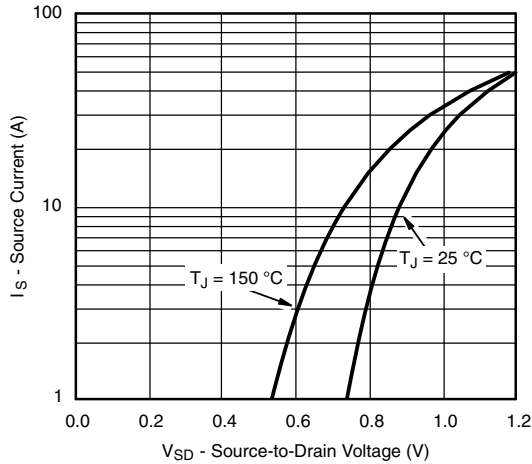
Gate Charge



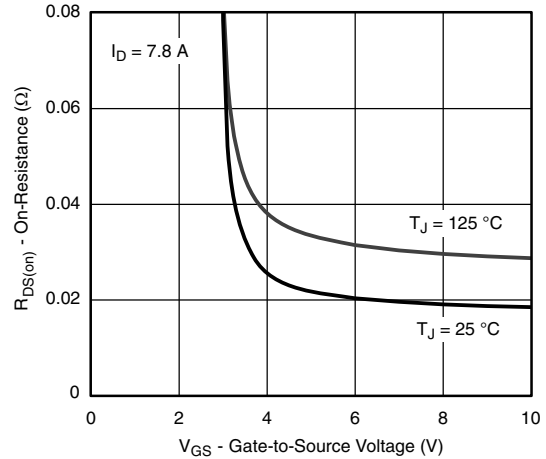
On-Resistance vs. Junction Temperature



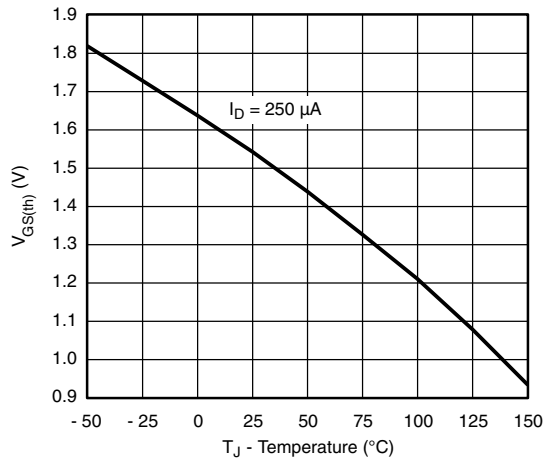
CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



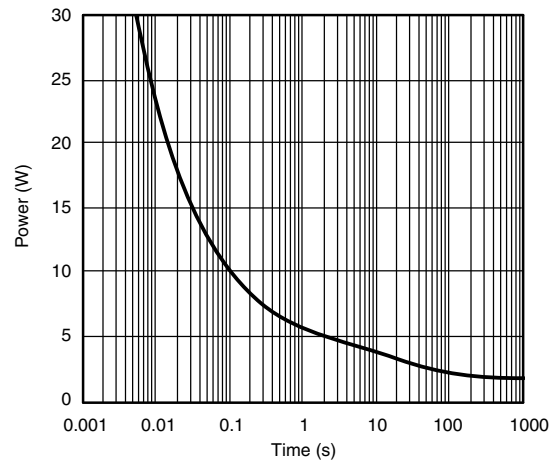
Source-Drain Diode Forward Voltage



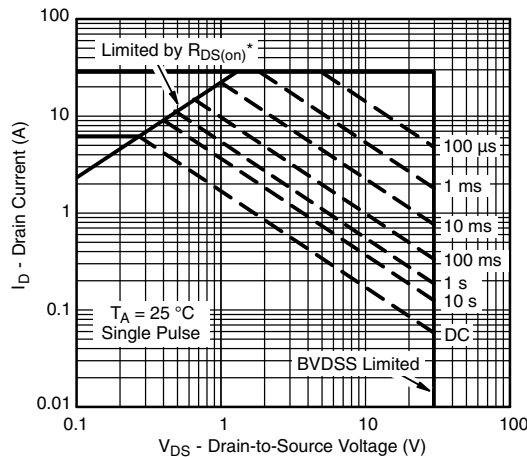
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



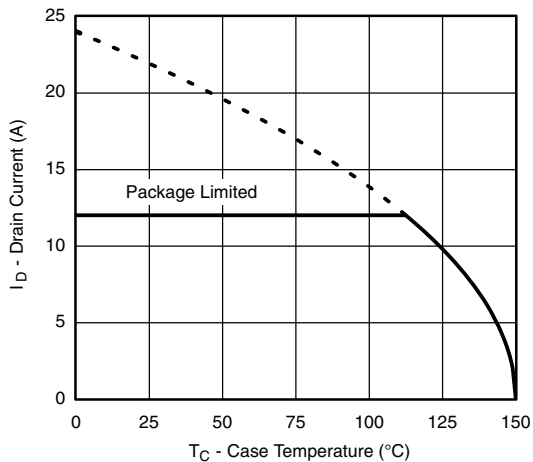
Safe Operating Area, Junction-to-Ambient

SiZ704DT

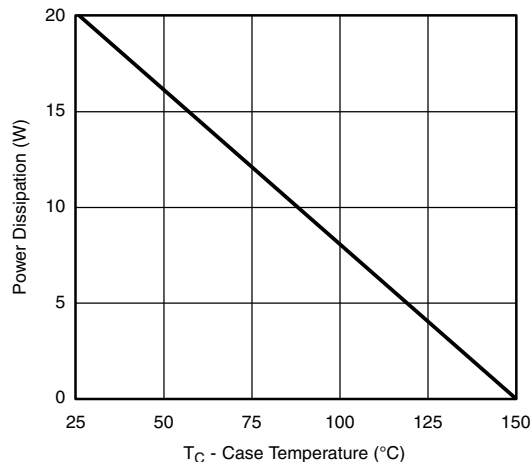
Vishay Siliconix



CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*

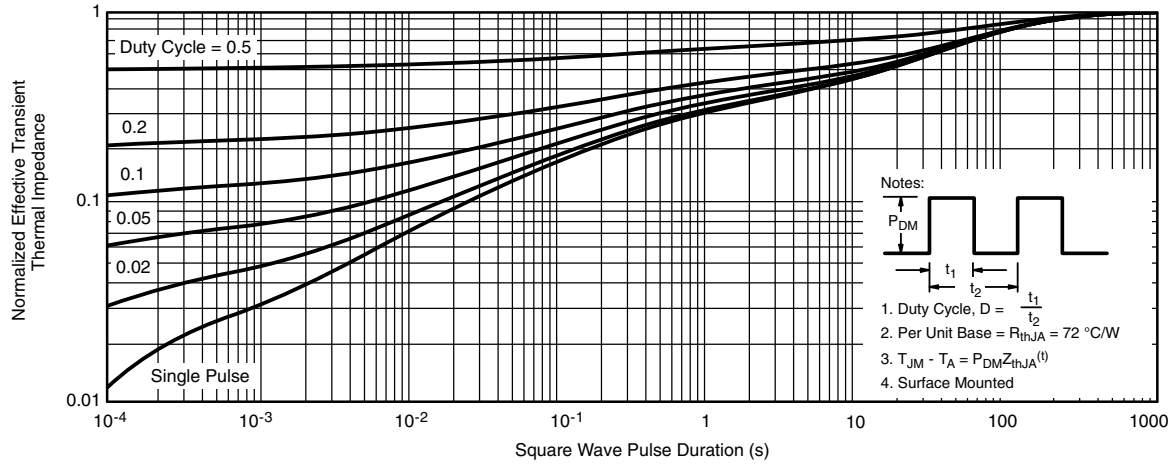


Power, Junction-to-Case

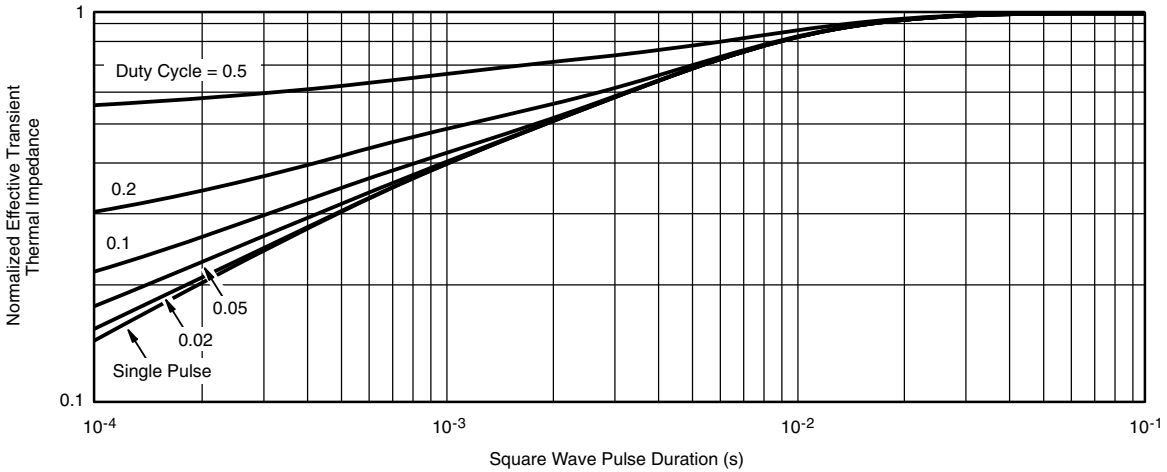
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



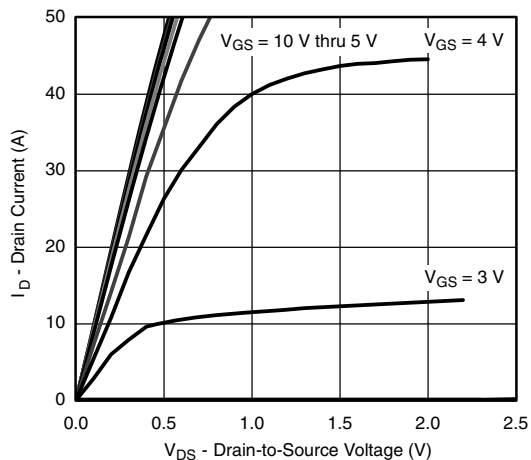
Normalized Thermal Transient Impedance, Junction-to-Case

SiZ704DT

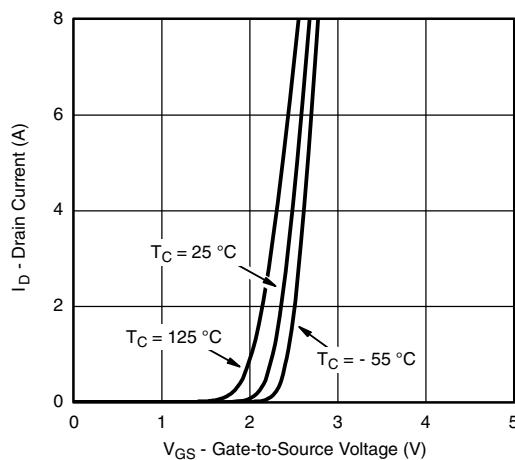
Vishay Siliconix



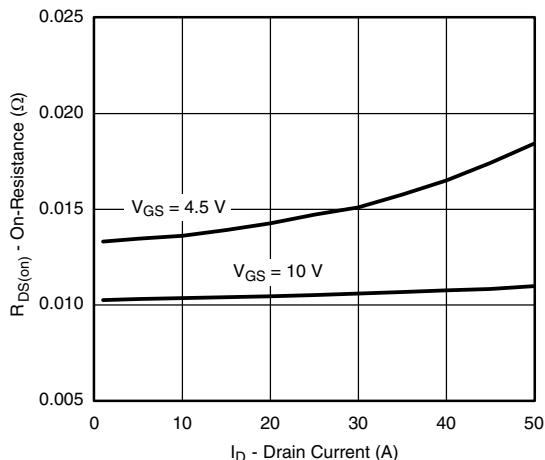
CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



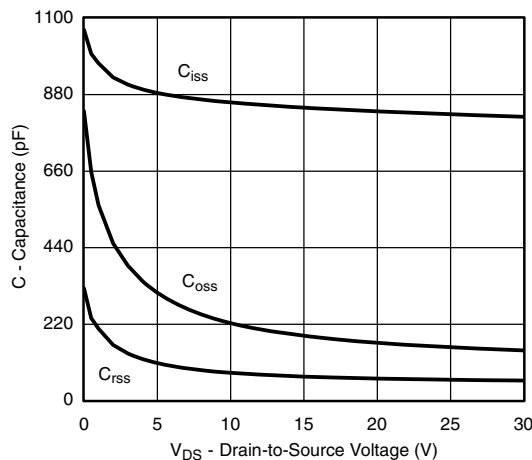
Output Characteristics



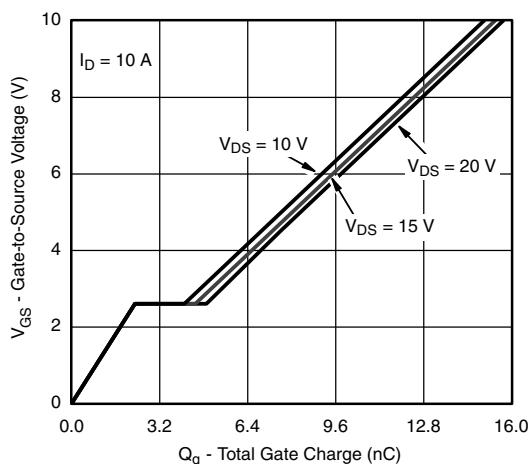
Transfer Characteristics



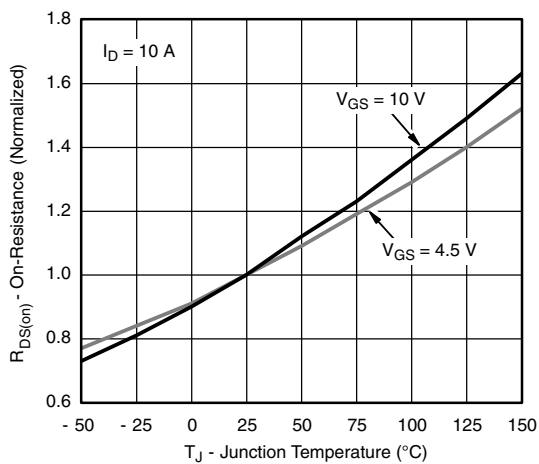
On-Resistance vs. Drain Current



Capacitance



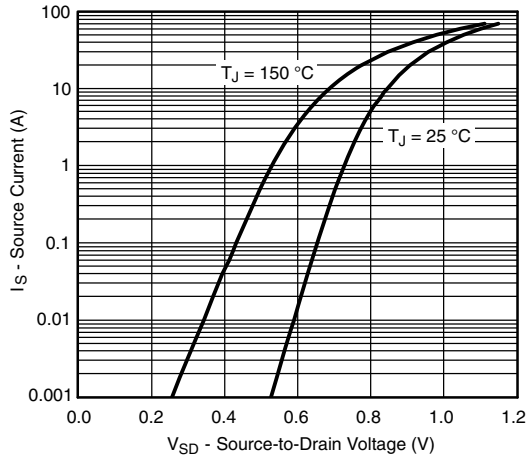
Gate Charge



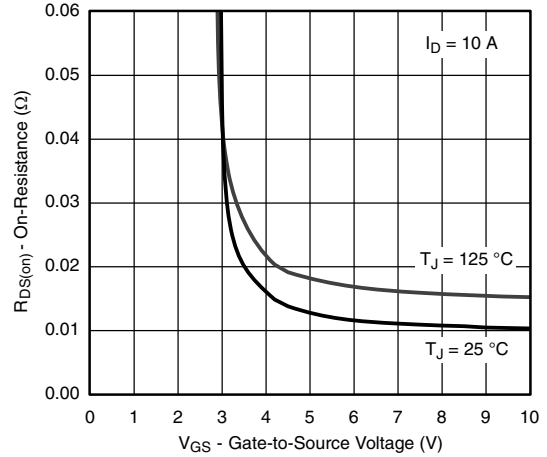
On-Resistance vs. Junction Temperature



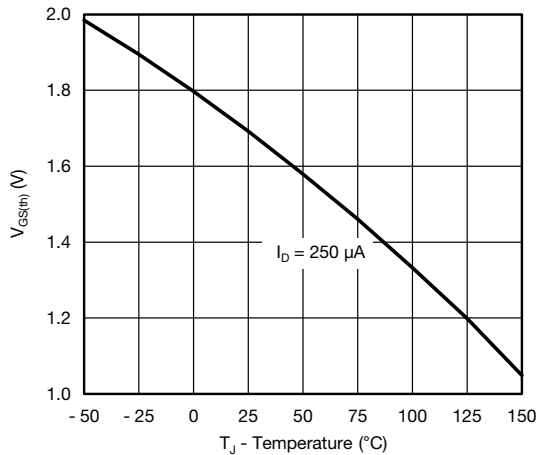
CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



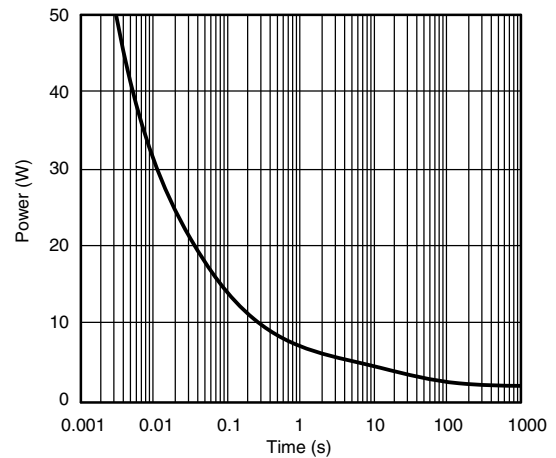
Source-Drain Diode Forward Voltage



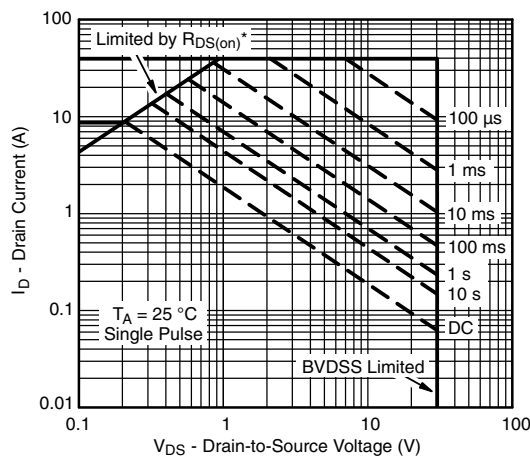
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



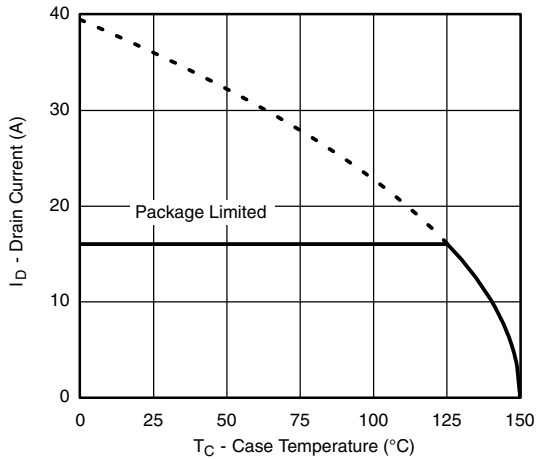
Safe Operating Area, Junction-to-Ambient

SiZ704DT

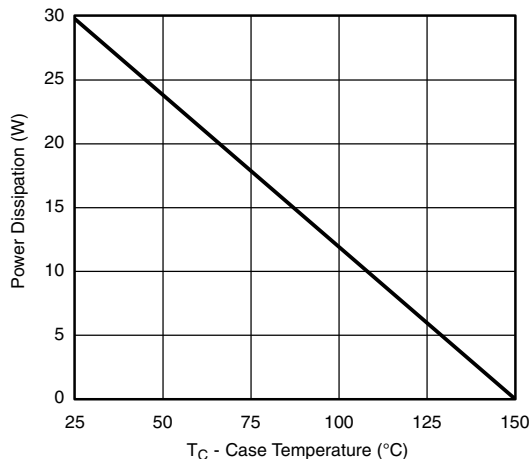
Vishay Siliconix



CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*

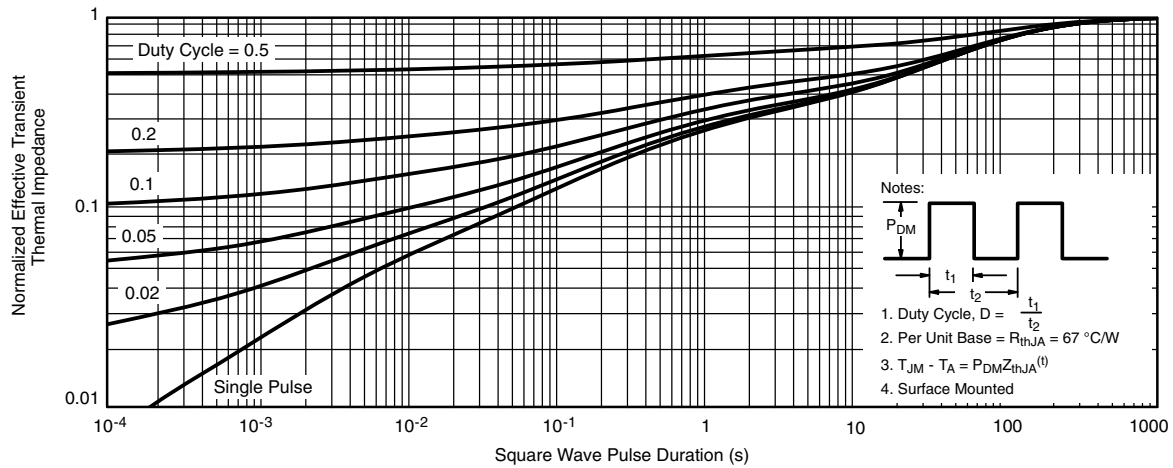


Power, Junction-to-Case

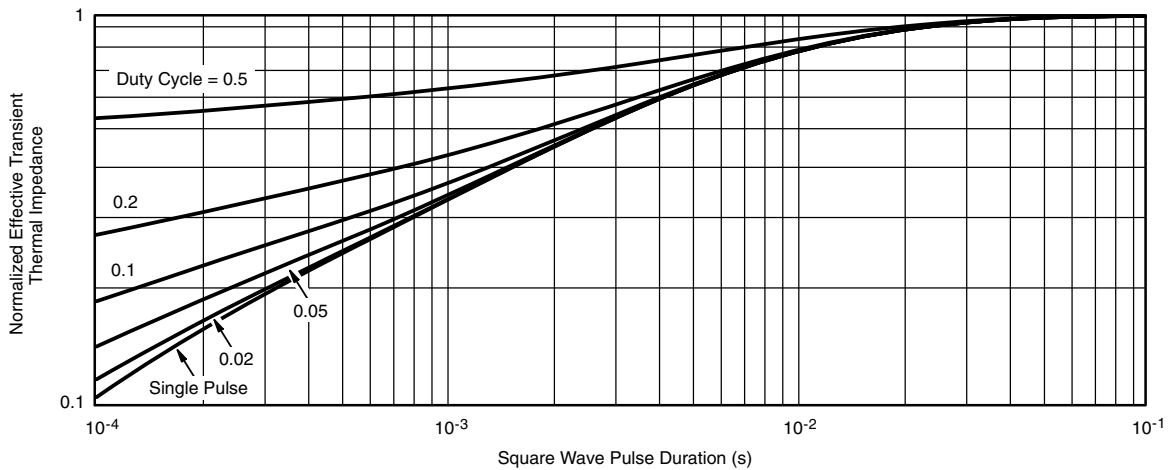
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



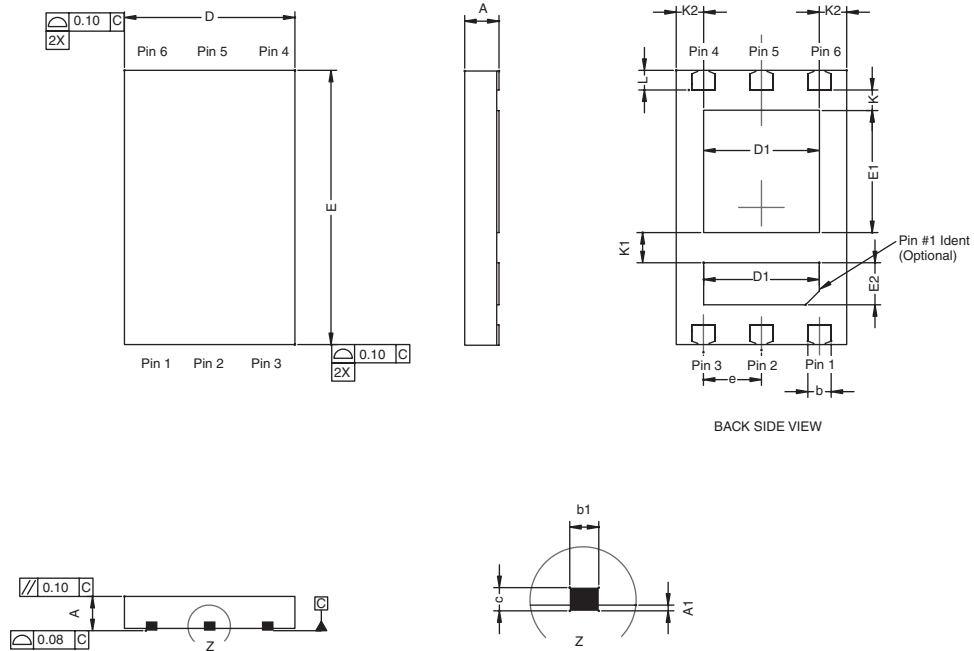
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65367.

PowerPAIR™ 6 x 3.7 CASE OUTLINE



| DIM. | MILLIMETERS | | | INCHES | | |
|---|-------------|------|------|------------|-------|-------|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| A | 0.70 | 0.75 | 0.80 | 0.028 | 0.030 | 0.032 |
| A1 | 0.00 | - | 0.05 | 0.000 | - | 0.002 |
| b | 0.46 | 0.51 | 0.56 | 0.018 | 0.020 | 0.022 |
| b1 | 0.20 | 0.25 | 0.38 | 0.008 | 0.010 | 0.015 |
| C | 0.18 | 0.20 | 0.23 | 0.007 | 0.008 | 0.009 |
| D | 3.65 | 3.73 | 3.81 | 0.144 | 0.147 | 0.150 |
| D1 | 2.41 | 2.53 | 2.65 | 0.095 | 0.100 | 0.104 |
| E | 5.92 | 6.00 | 6.08 | 0.233 | 0.236 | 0.239 |
| E1 | 2.62 | 2.67 | 2.72 | 0.103 | 0.105 | 0.107 |
| E2 | 0.87 | 0.92 | 0.97 | 0.034 | 0.036 | 0.038 |
| e | 1.27 BSC | | | 0.05 BSC | | |
| K | 0.45 TYP. | | | 0.018 TYP. | | |
| K1 | 0.66 TYP. | | | 0.026 TYP. | | |
| K2 | 0.60 TYP. | | | 0.024 TYP. | | |
| L | 0.38 | 0.43 | 0.48 | 0.015 | 0.017 | 0.019 |
| ECN: S-82772-Rev. B, 17-Nov-08 DWG: 5979 | | | | | | |

RECOMMENDED PAD FOR PowerPAIR™ 6 x 3.7



Recommended PAD for PowerPAIR 6 x 3.7
 Dimensions in inches (mm)
 Keep-out 0.3520 (8.94) x 0.4390 (11.151)



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